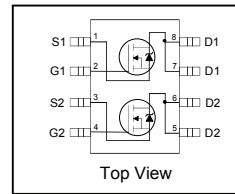


Features

- Advanced Planar Technology
- Dual N Channel MOSFET
- Low On-Resistance
- Logic Level Gate Drive
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *

Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



| | |
|-------------------|--------------|
| V_{DSS} | 30V |
| $R_{DS(on)}$ max. | 0.05Ω |
| I_D | 5.3A |



| | | |
|----------|----------|----------|
| G | D | S |
| Gate | Drain | Source |

| Base part number | Package Type | Standard Pack | | Orderable Part Number |
|------------------|--------------|---------------|----------|-----------------------|
| | | Form | Quantity | |
| AUIRF7303Q | SO-8 | Tape and Reel | 4000 | AUIRF7303QTR |

Absolute Maximum Ratings

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

| Symbol | Parameter | Max. | Units |
|--------------------------|---|--------------|-------|
| $I_D @ T_A = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 5.3 | A |
| $I_D @ T_A = 70^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 4.4 | |
| I_{DM} | Pulsed Drain Current ① | 44 | |
| $P_D @ T_A = 25^\circ C$ | Maximum Power Dissipation | 2.4 | W |
| | Linear Derating Factor | 0.02 | W/°C |
| V_{GS} | Gate-to-Source Voltage | ± 20 | V |
| E_{AS} | Single Pulse Avalanche Energy (Thermally Limited) ② | 414 | mJ |
| $E_{AS (Tested)}$ | Single Pulse Avalanche Energy (Thermally Limited) ⑤ | 1160 | |
| dv/dt | Peak Diode Recovery dv/dt ③ | 1.6 | V/ns |
| T_J T_{STG} | Operating Junction and Storage Temperature Range | -55 to + 175 | °C |

Thermal Resistance

| Symbol | Parameter | Typ. | Max. | Units |
|-----------------|-----------------------|------|------|-------|
| $R_{\theta JA}$ | Junction-to-Ambient ⑥ | — | 62.5 | °C/W |

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*Qualification standards can be found at www.infineon.com

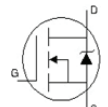
Static @ T_J = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|--------------------------------------|--------------------------------------|------|------|------|-------|---|
| V _{(BR)DSS} | Drain-to-Source Breakdown Voltage | 30 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| ΔV _{(BR)DSS/ΔT_J} | Breakdown Voltage Temp. Coefficient | — | 0.03 | — | V/°C | Reference to 25°C, I _D = 1mA |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | — | 0.05 | mΩ | V _{GS} = 10V, I _D = 2.7A ④ |
| | | — | — | 0.08 | | V _{GS} = 4.5V, I _D = 2.1A ④ |
| V _{GS(th)} | Gate Threshold Voltage | 1.0 | — | 3.0 | V | V _{DS} = V _{GS} , I _D = 100μA |
| g _{fs} | Forward Trans conductance | 5.6 | — | — | S | V _{DS} = 15V, I _D = 2.7A |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 1.0 | μA | V _{DS} = 24V, V _{GS} = 0V |
| | | — | — | 25 | | V _{DS} = 24V, V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | 100 | nA | V _{GS} = 20V |
| | Gate-to-Source Reverse Leakage | — | — | -100 | | V _{GS} = -20V |

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

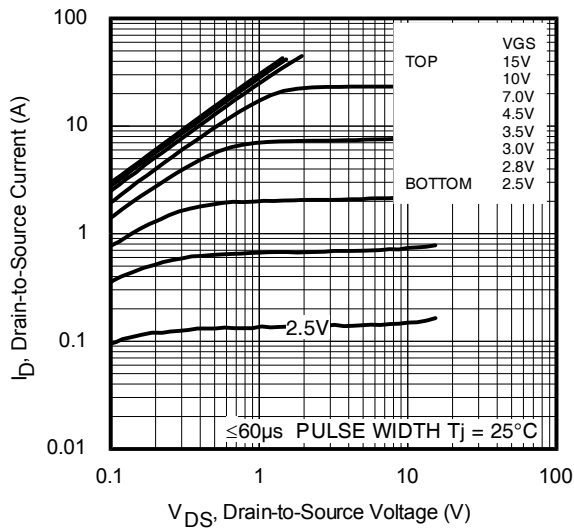
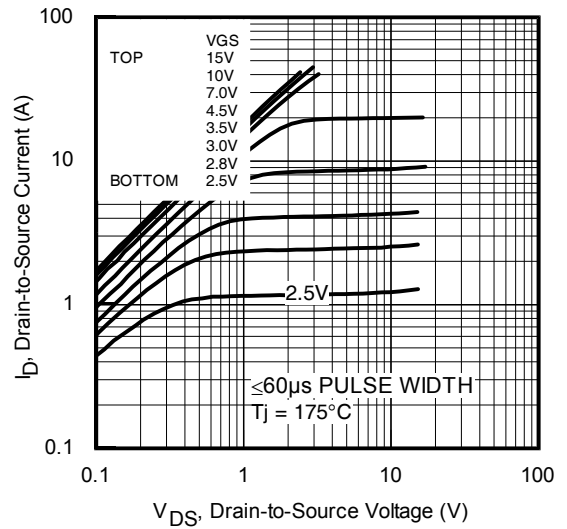
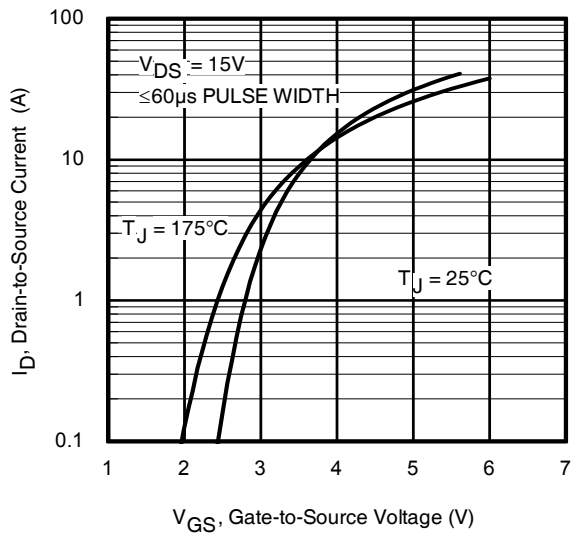
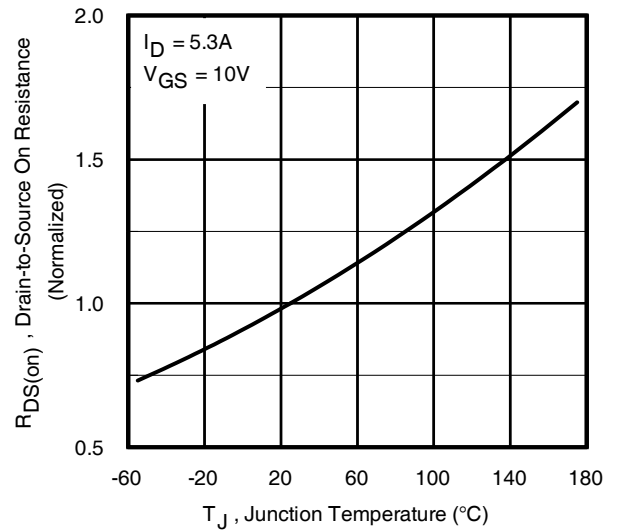
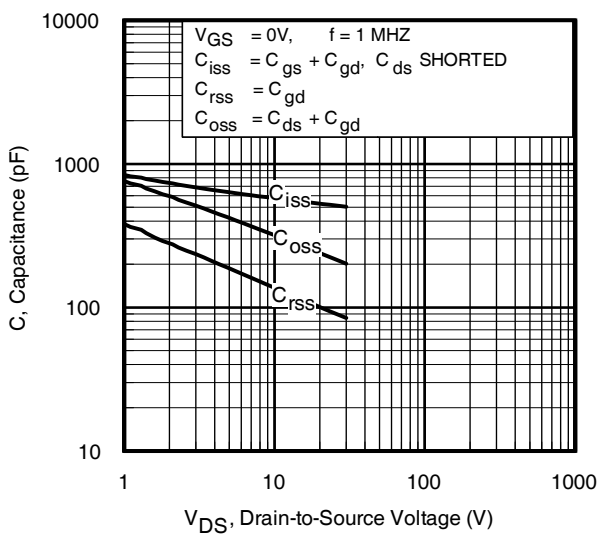
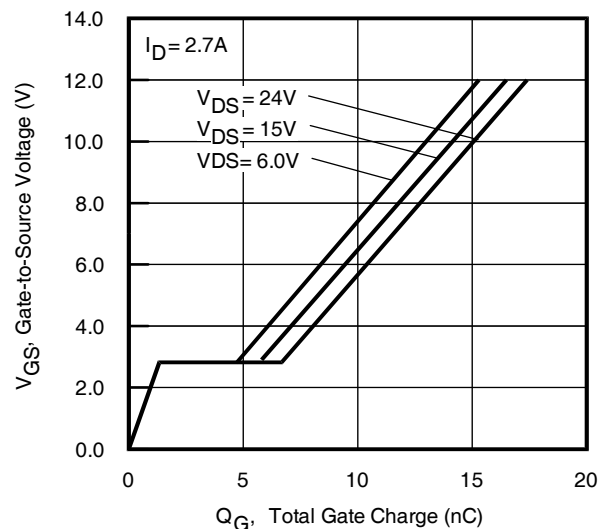
| | | | | | | |
|---------------------|------------------------------|---|-----|-----|----|-------------------------|
| Q _g | Total Gate Charge | — | 14 | 21 | nC | I _D = 2.7A |
| Q _{gs} | Gate-to-Source Charge | — | 1.5 | 2.3 | | V _{DS} = 15V |
| Q _{gd} | Gate-to-Drain Charge | — | 4.4 | 6.6 | | V _{GS} = 10V ④ |
| t _{d(on)} | Turn-On Delay Time | — | 2.9 | — | ns | V _{DD} = 15V |
| t _r | Rise Time | — | 6.2 | — | | I _D = 2.7A |
| t _{d(off)} | Turn-Off Delay Time | — | 15 | — | | R _G = 6.8Ω |
| t _f | Fall Time | — | 7.8 | — | | V _{GS} = 10V ④ |
| C _{iss} | Input Capacitance | — | 515 | — | pF | V _{GS} = 0V |
| C _{oss} | Output Capacitance | — | 217 | — | | V _{DS} = 25V |
| C _{rss} | Reverse Transfer Capacitance | — | 90 | — | | f = 1.0MHz |

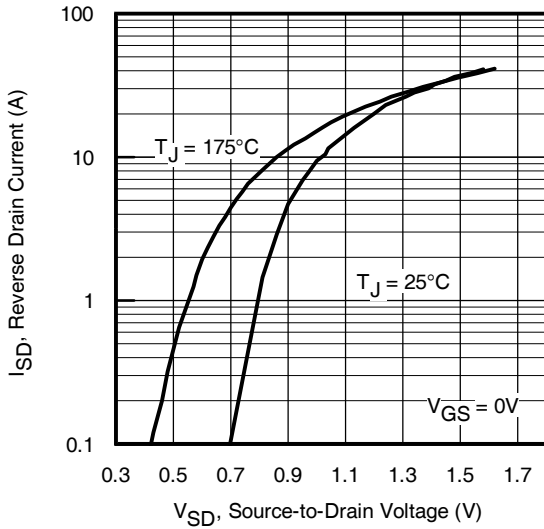
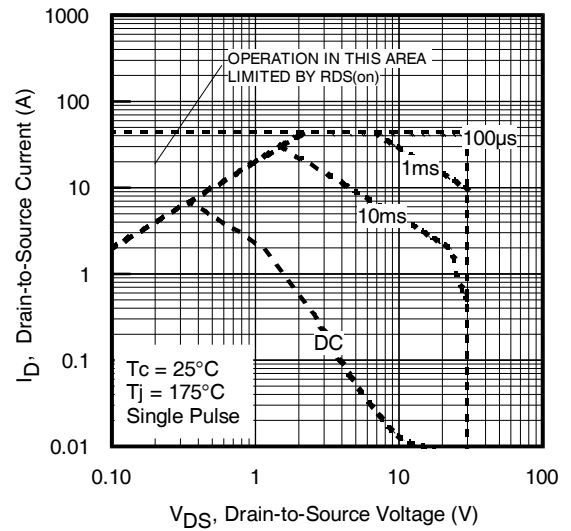
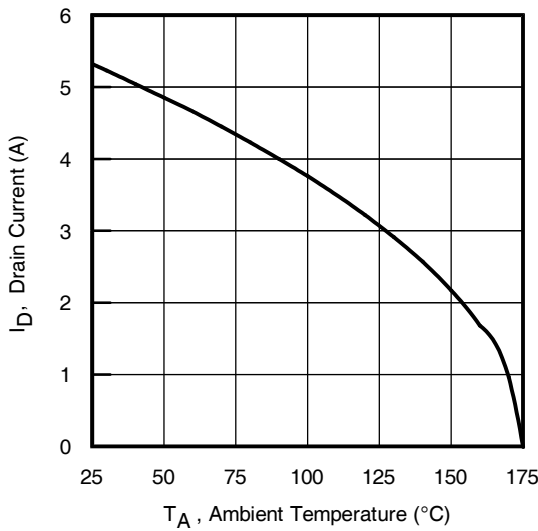
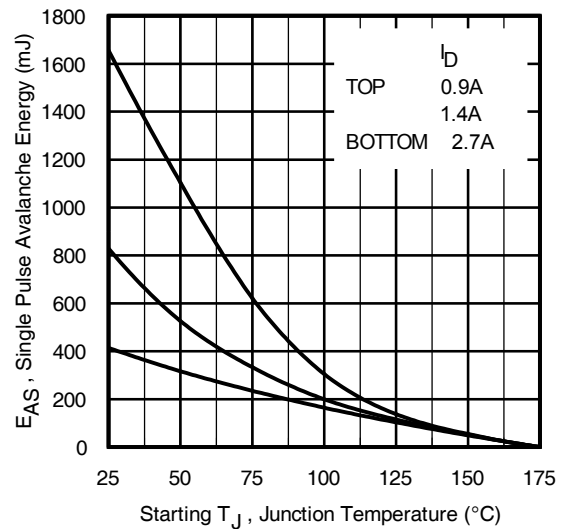
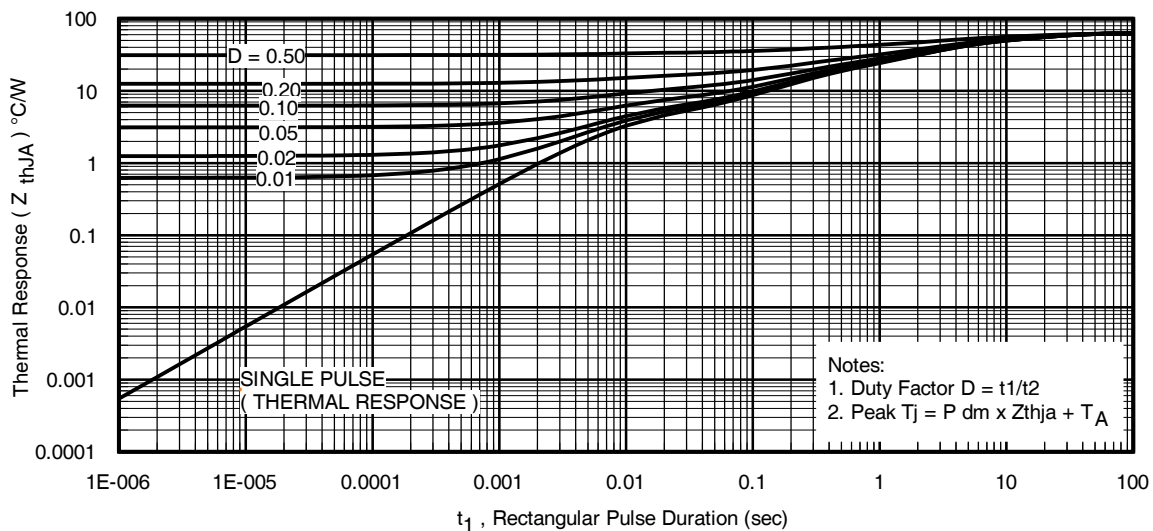
Diode Characteristics

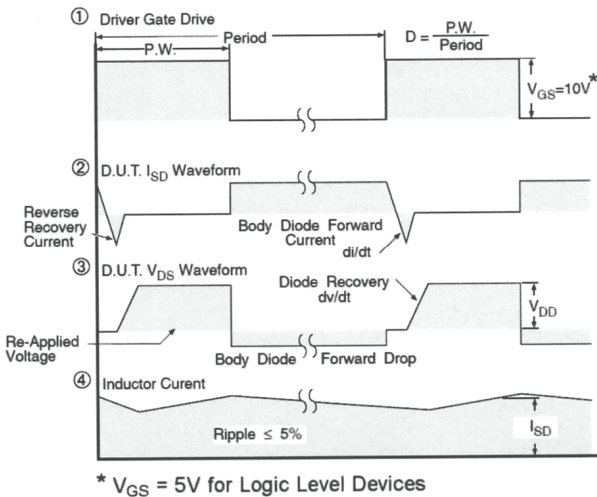
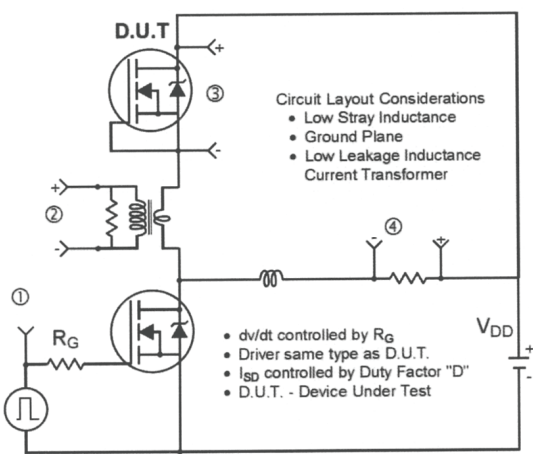
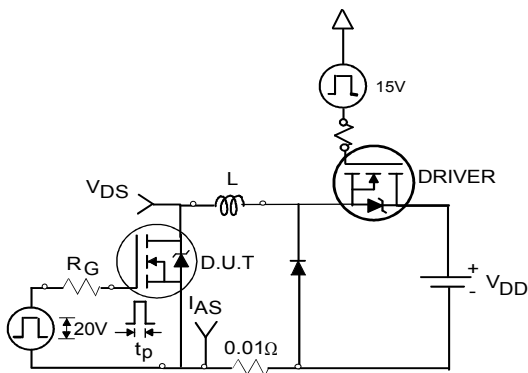
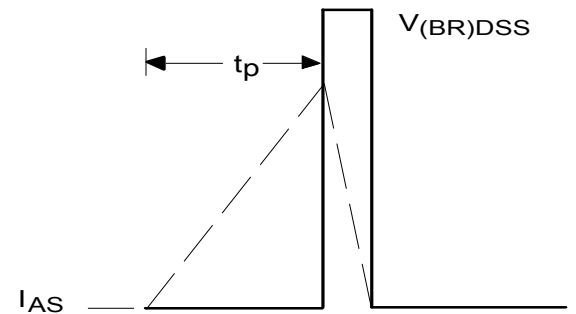
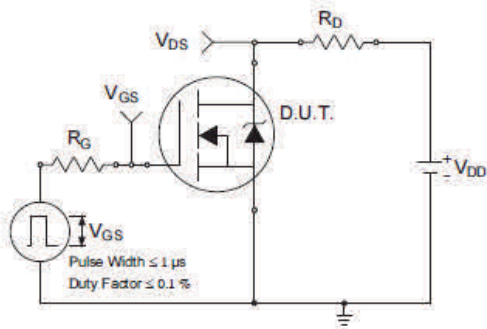
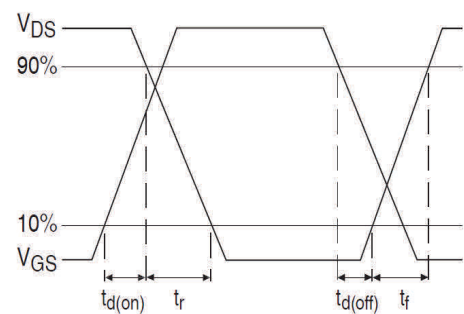
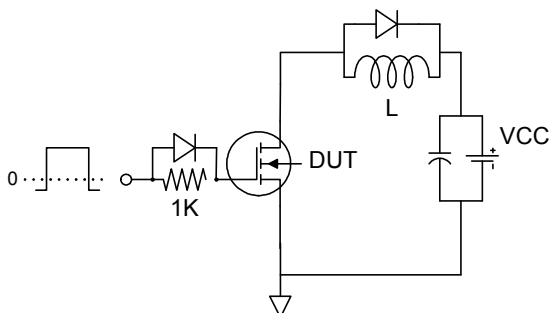
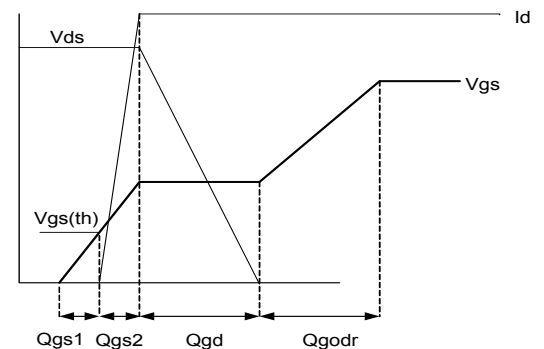
| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-----------------|--|------|------|------|-------|--|
| I _S | Continuous Source Current (Body Diode) | — | — | 3.0 | A | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I _{SM} | Pulsed Source Current (Body Diode) ① | — | — | 44 | | |
| V _{SD} | Diode Forward Voltage | — | — | 1.0 | V | T _J = 25°C, I _S = 2.7A, V _{GS} = 0V ④ |
| t _{rr} | Reverse Recovery Time | — | 26 | 39 | ns | T _J = 25°C, I _F = 2.7A, |
| Q _{rr} | Reverse Recovery Charge | — | 50 | 75 | nC | di/dt = 100A/μs ④ |

Notes:

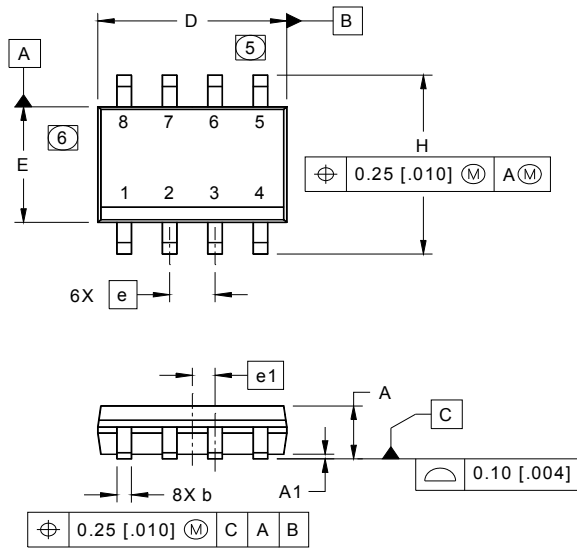
- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{Jmax}, Starting T_J = 25°C, L = 118mH, R_G = 50Ω, I_{AS} = 2.7A V_{GS} = 10V. Part not recommended for use above this value.
- ③ I_{SD} ≤ 2.7A, di/dt ≤ 389A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C.
- ④ Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ⑤ This value determined from sample failure population, T_J = 25°C, L = 118mH, R_G = 50Ω, I_{AS} = 2.7A, V_{GS} = 10V.
- ⑥ Surface mounted on FR-4 board, t ≤ 10sec.


Fig. 1 Typical Output Characteristics

Fig. 2 Typical Output Characteristics

Fig. 3 Typical Transfer Characteristics

Fig. 4 Normalized On-Resistance vs. Temperature

Fig. 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig. 6. Typical Gate Charge vs. Gate-to-Source Voltage

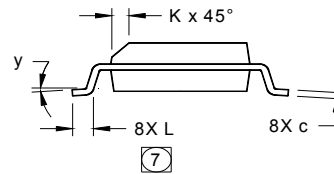

Fig. 7 Typical Source-to-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

Fig 9. Maximum Drain Current vs. Case Temperature

Fig 10. Maximum Avalanche Energy vs. Drain Current

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient


Fig 12. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET[®] Power MOSFETs

Fig 13a. Unclamped Inductive Test Circuit

Fig 13b. Unclamped Inductive Waveforms

Fig 14a. Switching Time Test Circuit

Fig 14b. Switching Time Waveforms

Fig 15a. Gate Charge Test Circuit

Fig 15b. Gate Charge Waveform

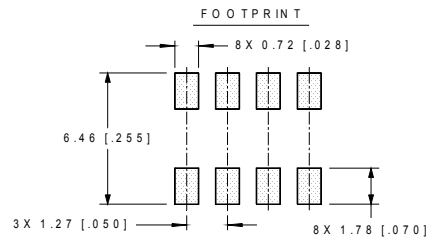
SO-8 Package Outline (Dimensions are shown in millimeters (inches))



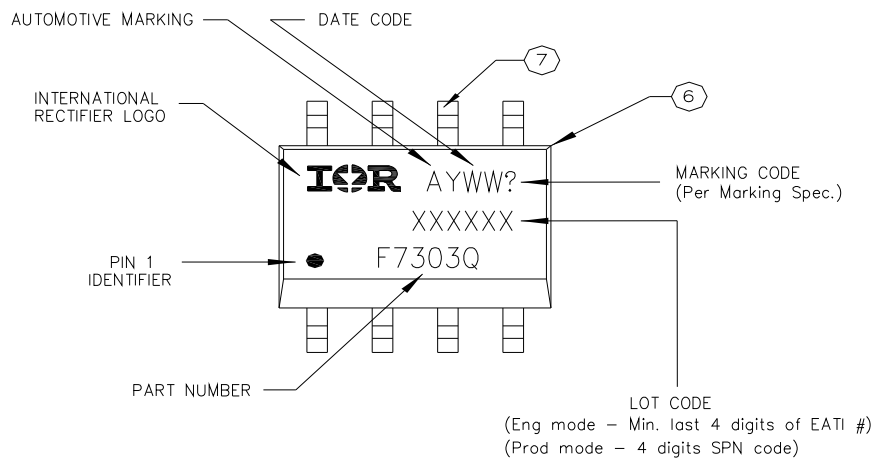
| DIM | INCHES | | MILLIMETERS | |
|-----|------------|-------|-------------|------|
| | MIN | MAX | MIN | MAX |
| A | .0532 | .0688 | 1.35 | 1.75 |
| A1 | .0040 | .0098 | 0.10 | 0.25 |
| b | .013 | .020 | 0.33 | 0.51 |
| c | .0075 | .0098 | 0.19 | 0.25 |
| D | .189 | .1968 | 4.80 | 5.00 |
| E | .1497 | .1574 | 3.80 | 4.00 |
| e | .050 BASIC | | 1.27 BASIC | |
| e 1 | .025 BASIC | | 0.635 BASIC | |
| H | .2284 | .2440 | 5.80 | 6.20 |
| K | .0099 | .0196 | 0.25 | 0.50 |
| L | .016 | .050 | 0.40 | 1.27 |
| y | 0° | 8° | 0° | 8° |



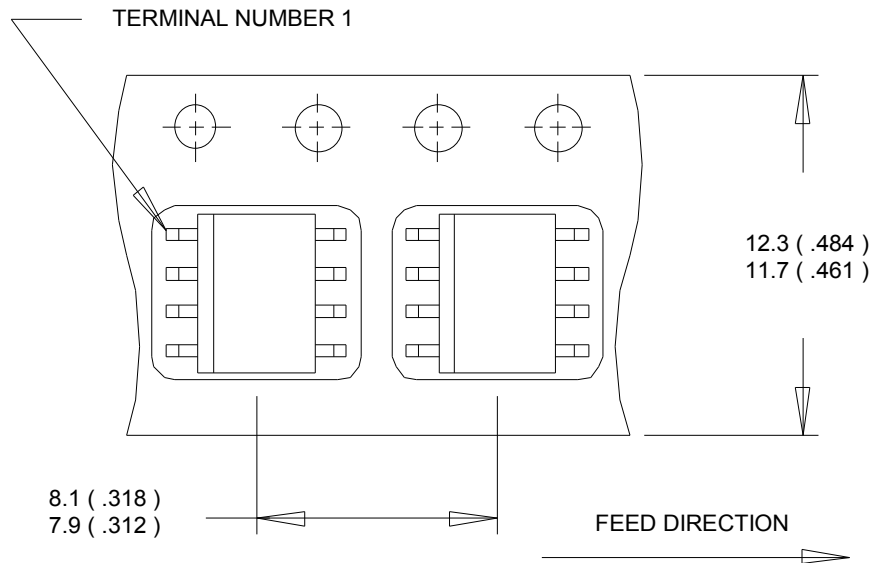
- NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: MILLIMETER
 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
 5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
 6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
 7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



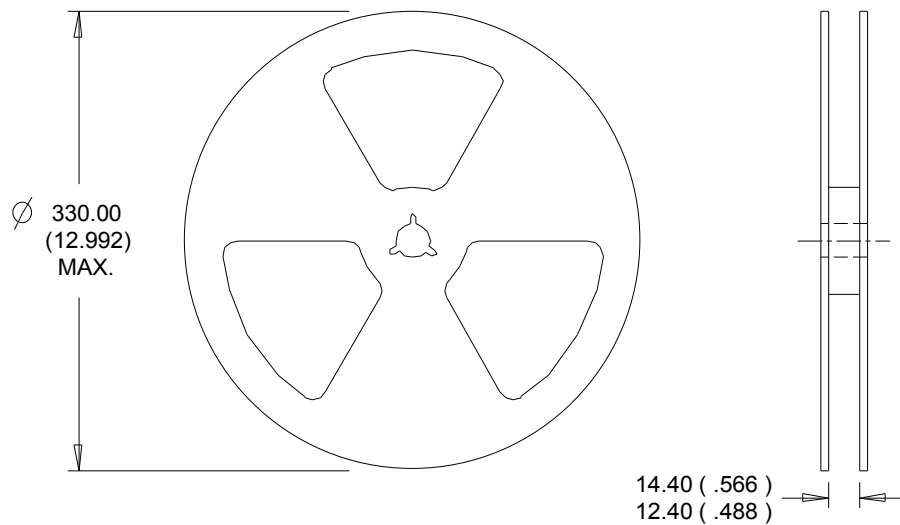
SO-8 Part Marking Information



TOP MARKING (LASER)

SO-8 Tape and Reel (Dimensions are shown in millimeters (inches))

NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.


NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Qualification Information

| | | | |
|-----------------------------------|----------------------|---|------|
| Qualification Level | | Automotive (per AEC-Q101) | |
| | | Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level. | |
| Moisture Sensitivity Level | | SO-8 | MSL1 |
| ESD | Machine Model | Class M2 (+/- 150V) [†] AEC-Q101-002 | |
| | Human Body Model | Class H1A (+/- 500V) [†] AEC-Q101-001 | |
| | Charged Device Model | Class C5 (+/- 1500V) [†] AEC-Q101-005 | |
| RoHS Compliant | | Yes | |

† Highest passing voltage.

Revision History

| Date | Comments |
|-----------|--|
| 3/4/2014 | <ul style="list-style-type: none"> Added "Logic Level Gate Drive" bullet in the features section on page 1 Updated data sheet with new IR corporate template |
| 9/30/2015 | <ul style="list-style-type: none"> Updated datasheet with corporate template Corrected ordering table on page 1. |

Published by
Infineon Technologies AG
81726 München, Germany
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